

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCTS CHARACTERISTICS

| | |
|----------------------------|----------------|
| I_{F(AV)} | 2 x 8 A |
| V_{RRM} | 45 V |
| T_{j (max)} | 150 °C |
| V_{F (max)} | 0.45 V |

FEATURES AND BENEFITS

- Low forward voltage drop meaning very small conduction losses
- Low switching losses allowing high frequency operation
- Insulated package: TO-220FPAB
Insulated voltage: 2000V DC
Capacitance: 12 pF

DESCRIPTION

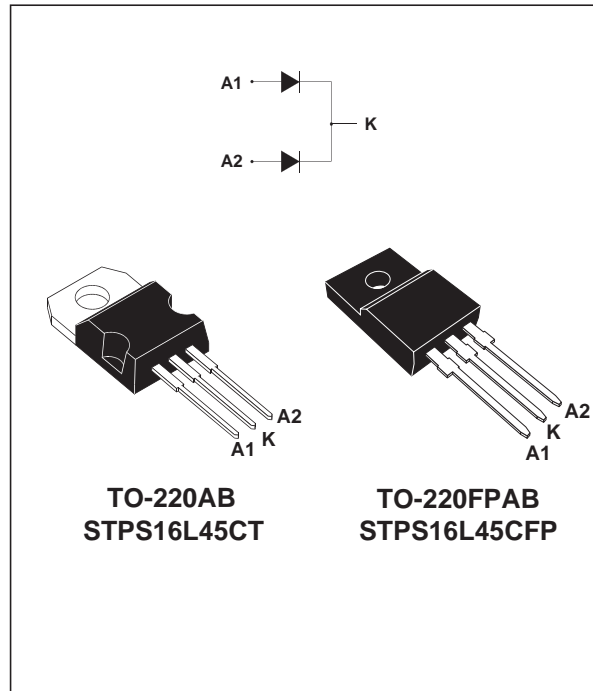
Dual center tap Schottky barrier rectifier designed for high frequency Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in TO-220AB and TO-220FPAB, these devices are intended for use in low voltage, high frequency converters, free-wheeling and polarity protection applications.

ABSOLUTE RATINGS (limiting values, per diode)

| Symbol | Parameter | | | Value | Unit | |
|---------------------|--|------------|-----------------------------------|---------------|------|---|
| V _{RRM} | Repetitive peak reverse voltage | | | 45 | V | |
| I _{F(RMS)} | RMS forward current | | | 30 | A | |
| I _{F(AV)} | Average forward current | TO-220AB | T _c = 140°C δ = 0.5 | Per diode | 8 | A |
| | | | Per device | 16 | | |
| | | TO-220FPAB | T _c = 125°C δ = 0.5 | Per diode | 8 | A |
| | | | | Per device | 16 | |
| I _{FSM} | Surge non repetitive forward current | | tp = 10 ms sinusoidal | 180 | A | |
| I _{RRM} | Repetitive peak reverse current | | tp=2 μs square F=1kHz | 1 | A | |
| I _{RSM} | Non repetitive peak reverse current | | tp = 100 μs square | 2 | A | |
| T _{stg} | Storage temperature range | | | - 65 to + 150 | °C | |
| T _j | Maximum operating junction temperature * | | | 150 | °C | |
| dV/dt | Critical rate of rise of reverse voltage | | | 10000 | V/μs | |

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink



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THERMAL RESISTANCES

| Symbol | Parameter | | Value | Unit |
|---------------|------------------|------------|-----------|------|
| $R_{th(j-c)}$ | Junction to case | TO-220AB | Per diode | 2.2 |
| | | | Total | 1.3 |
| | | TO-220FPAB | Per diode | 4.5 |
| | | | Total | 3.5 |
| | | | Coupling | 0.3 |
| | | | Coupling | 2.5 |

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

| Symbol | Parameter | Tests Conditions | | Min. | Typ. | Max. | Unit |
|---------|-------------------------|---------------------------|---------------------|------|------|------|------|
| I_R^* | Reverse leakage current | $T_j = 25^\circ\text{C}$ | $V_R = V_{RRM}$ | | | 0.2 | mA |
| | | $T_j = 125^\circ\text{C}$ | | | 65 | 130 | mA |
| V_F^* | Forward voltage drop | $T_j = 25^\circ\text{C}$ | $I_F = 8\text{ A}$ | | | 0.5 | V |
| | | $T_j = 125^\circ\text{C}$ | $I_F = 8\text{ A}$ | | 0.39 | 0.45 | |
| | | $T_j = 25^\circ\text{C}$ | $I_F = 16\text{ A}$ | | | 0.63 | |
| | | $T_j = 125^\circ\text{C}$ | $I_F = 16\text{ A}$ | | 0.55 | 0.64 | |

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.26 \times I_{F(AV)} + 0.024 I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

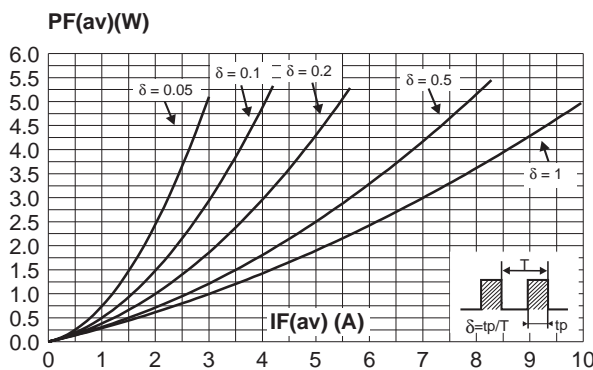


Fig. 2: Average current versus ambient temperature ($\delta = 0.5$) (per diode).

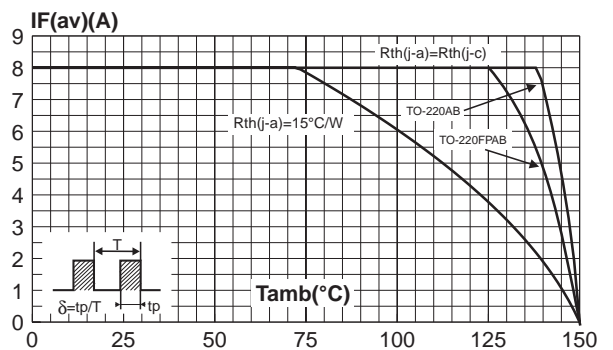


Fig. 3-1: Non repetitive surge peak forward current versus overload duration (maximum values per diode, TO-220AB).

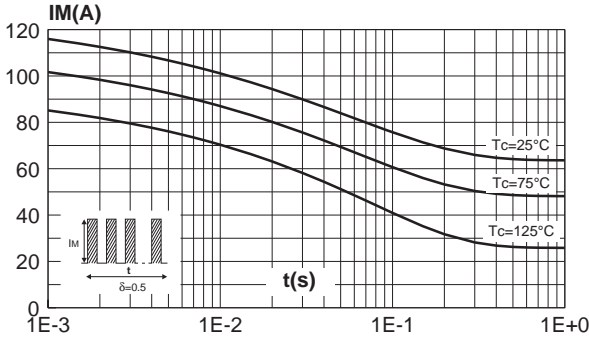


Fig. 3-2: Non repetitive surge peak forward current versus overload duration (maximum values per diode, TO-220FPAB).

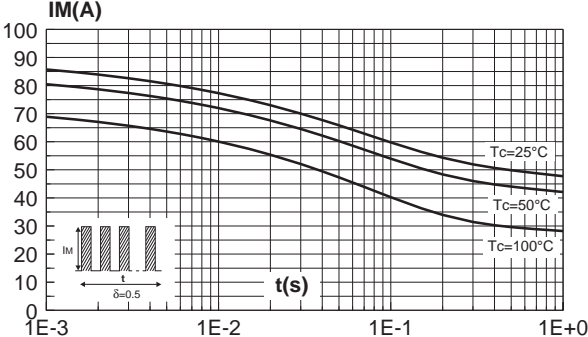


Fig. 4-1: Relative variation of thermal impedance junction to case versus pulse duration (TO-220AB).

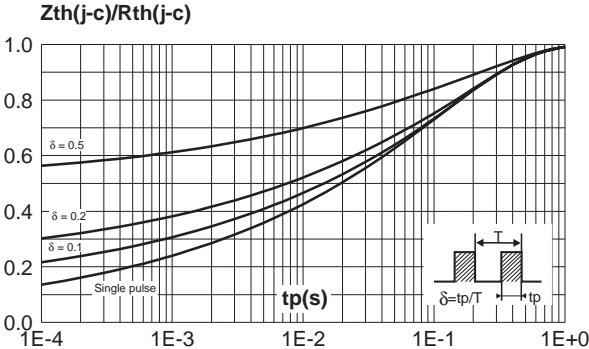


Fig. 4-2: Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAB).

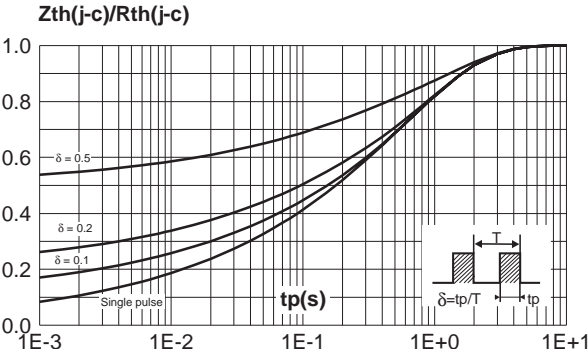


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values) (per diode).

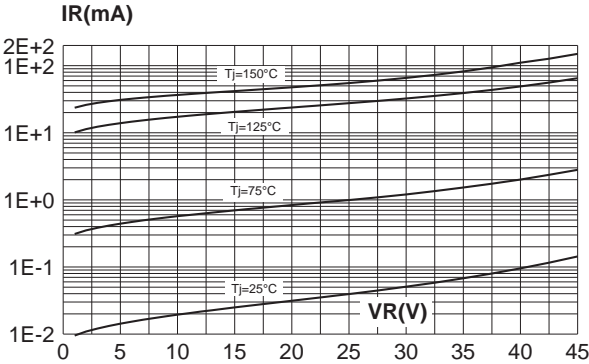
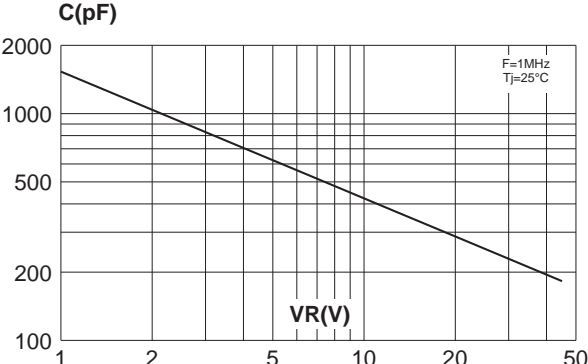
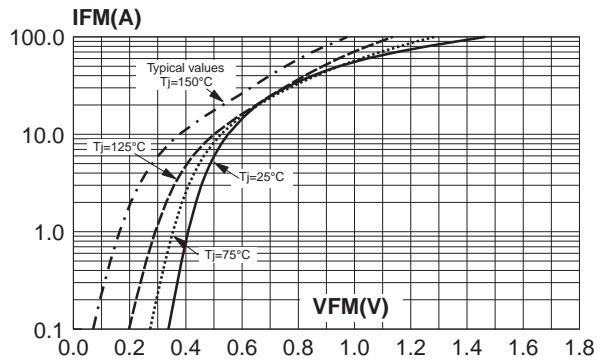


Fig. 6: Junction capacitance versus reverse voltage applied (typical values) (per diode).



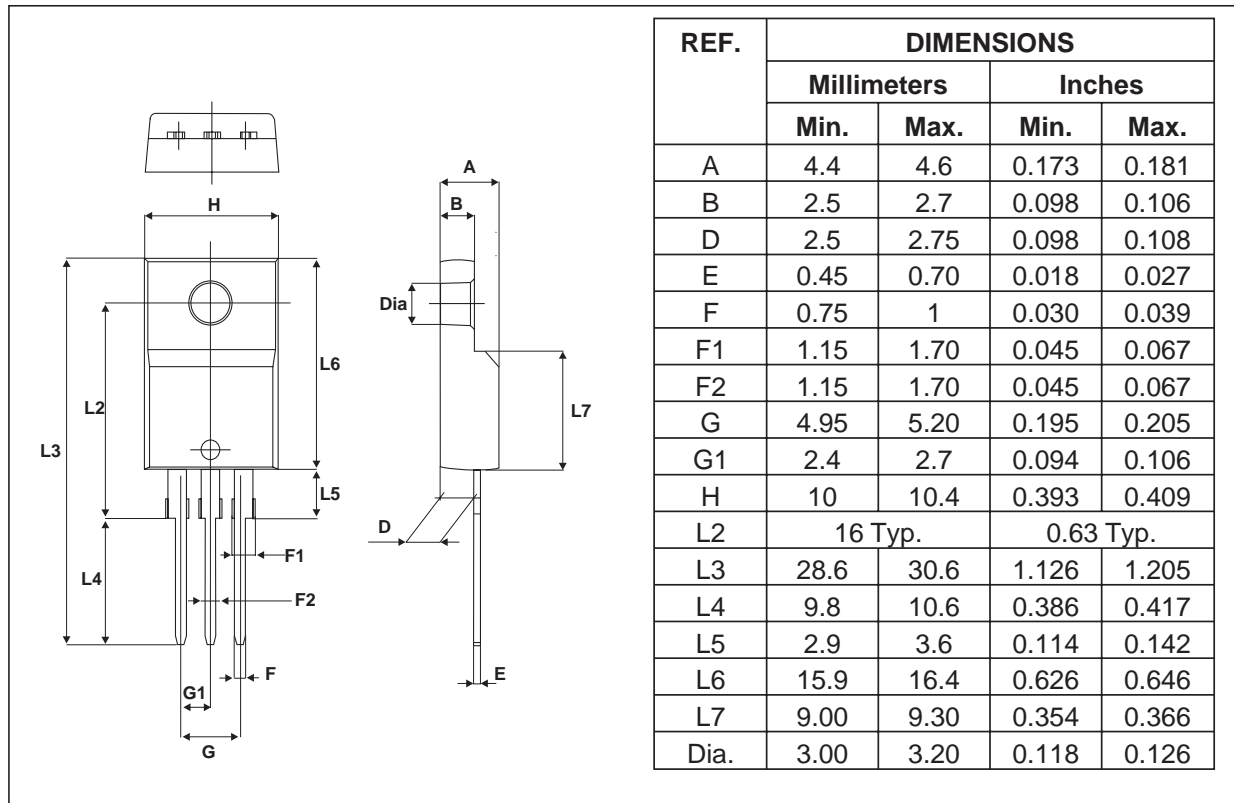
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Fig. 7: Forward voltage drop versus forward current (maximum values) (per diode).



PACKAGE MECHANICAL DATA

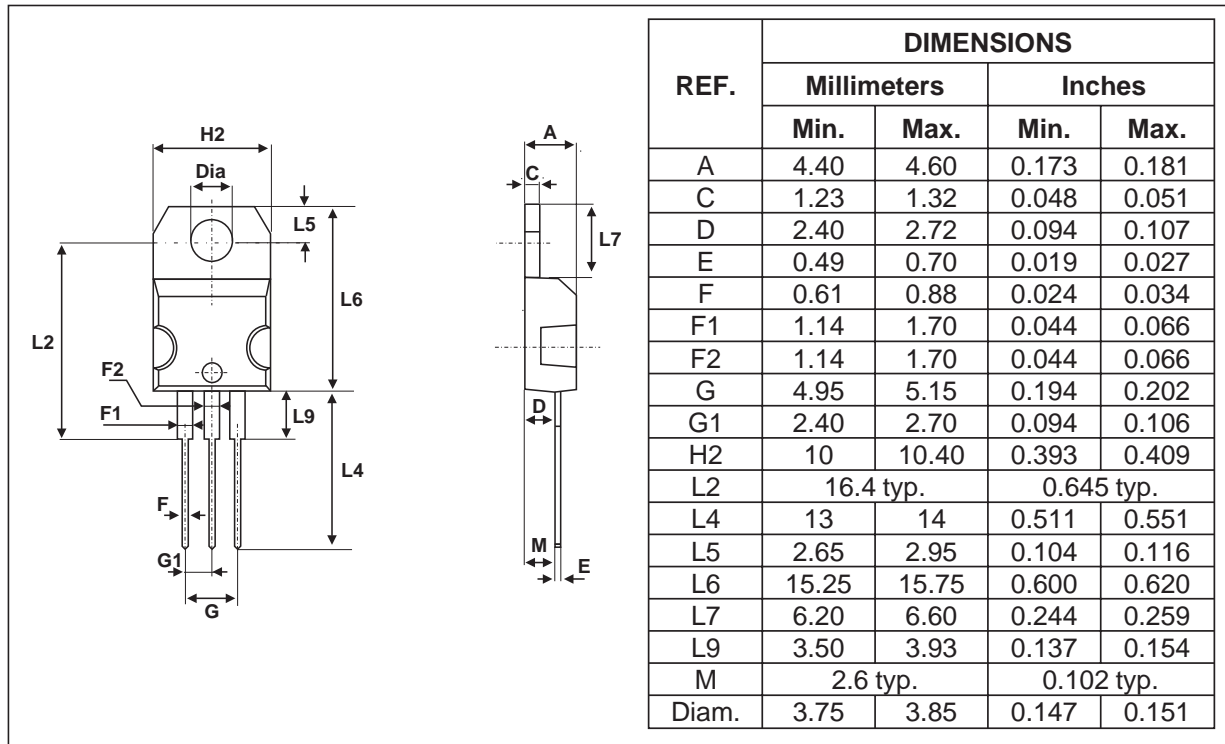
TO-220FPAB



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PACKAGE MECHANICAL DATA

TO-220AB



| Ordering type | Marking | Package | Weight | Base qty | Delivery mode |
|---------------|--------------|------------|--------|----------|---------------|
| STPS16L45CT | STPS16L45CT | TO-220AB | 2g | 50 | Tube |
| STPS16L45CFP | STPS16L45CFP | TO-220FPAB | 2g | 50 | Tube |

- Epoxy meets UL94,V0
- Cooling method : C
- Recommended torque value : 0.55 m.N

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